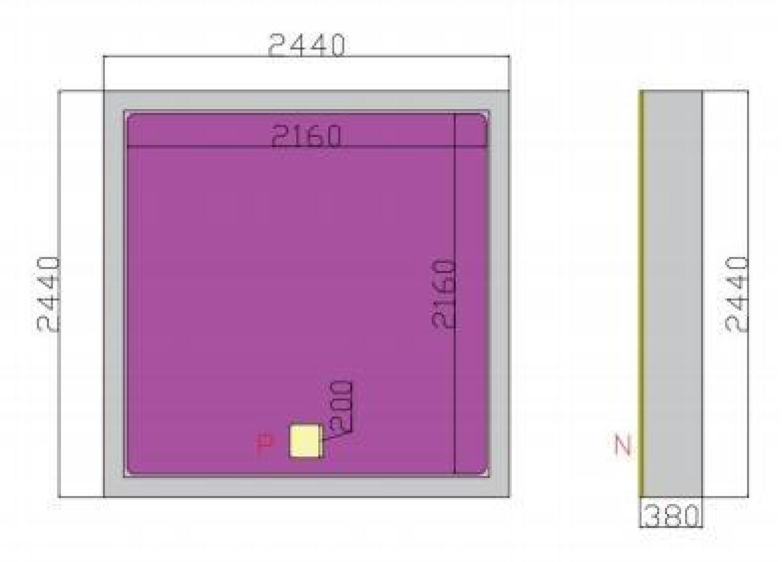
2.44mm Silicon PD Chip datasheet

P/N ：WS9B-01C



Application

Si PIN photodiode chip

Structure

Planar type：PIN diode
Electrodes :
Back side（Cathode）: Au
Top side (Anode) : Al

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	2160 x 2160 ± 15			μm
Chip width	2440			μm
Chip length	2440			μm
Chip height	360	380	400	μm
Pad Area	190	200	210	μm

Electro-Optical Characteristics（@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.7		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Sensitive Wavelength Range	λ		400	940	1100	nm
Reverse Dark Current	Id	Vr=10V			10	nA
Capacitance	Cj	VR=3V, f=1MHz		16		pF